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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	09/989969
				Filing Date	November 20, 2001
				First Named Inventor	David Kisailus
				Art Unit	N/A
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	LA-1279-342.US/10024731

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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
MAA	AA	6254675	07/03/2001	PUCHINGER MANFRED et al	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
MAA	BA	EP 0 295 467 A	12/21/1988	EASTMAN KODAK CO		

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¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MAA	CA	RODEWALD D ET AL: "GAN DERIVED FROM CARBODIIMIDE-BASED POLYMER PRECURSORS" ADVANCED MATERIALS, VCH VERLAGSGESELLSCHAFT, WEINHEIM, DE., vol. 11, no. 18, 17 December 1999, pages 1502-1504	

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Examiner Signature	Matthew Anderson	Date Considered	8/19/2003
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PAGE 1 OF 4

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

FEB 1 5 2002

Docket Number (Optional)

1279-342XX/1624731

Application Number

09/989,969

#4

Applicant(s)

DAVID J. KISAILUS, et al.

Filing Date

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Group Art Unit

Not Yet Assigned

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